

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

D44H10

DESCRIPTION

- With TO-220C package
- Fast switching speeds
- Low collector saturation voltage

APPLICATIONS

- For general purpose power amplification and switching regulators, converters and power amplifiers applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

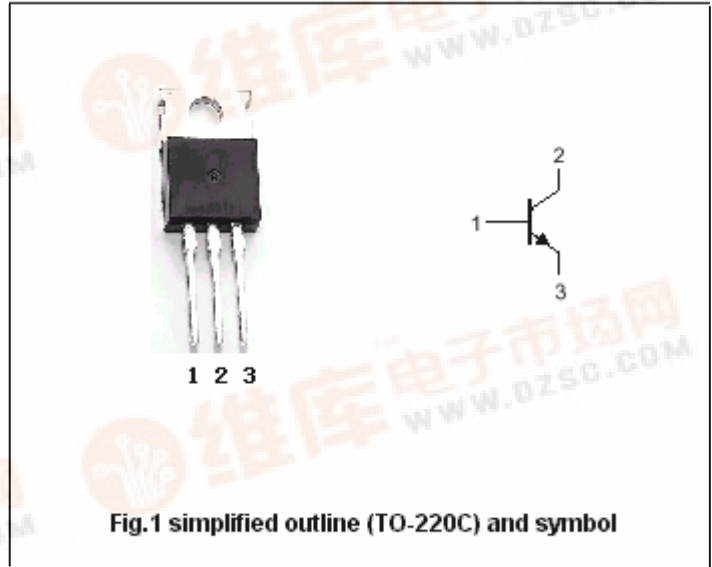


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings (Tc=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	80	V
V _{CEO}	Collector-emitter voltage	Open base	80	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		10	A
I _{CM}	Collector current-Peak		20	A
P _D	Total power dissipation	T _C =25	50	W
		T _a =25	1.67	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance from junction to case	2.5	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =10mA I _B =0,	80			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =8A ; I _B =0.8A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =8A ; I _B =0.8A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =80V; V _{BE} =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =2A ; V _{CE} =1V	35			
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =1V	20			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		50		MHz
C _{cb}	Collector capacitance	f=1MHz ; V _{CB} =10V		130		pF

Switching times

t _{on}	Turn-on time	I _C =5A I _{B1} =- I _{B2} =0.5A		0.3		μs
t _s	Storage time			0.5		μs
t _r	Fall time			0.14		μs

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PACKAGE OUTLINE

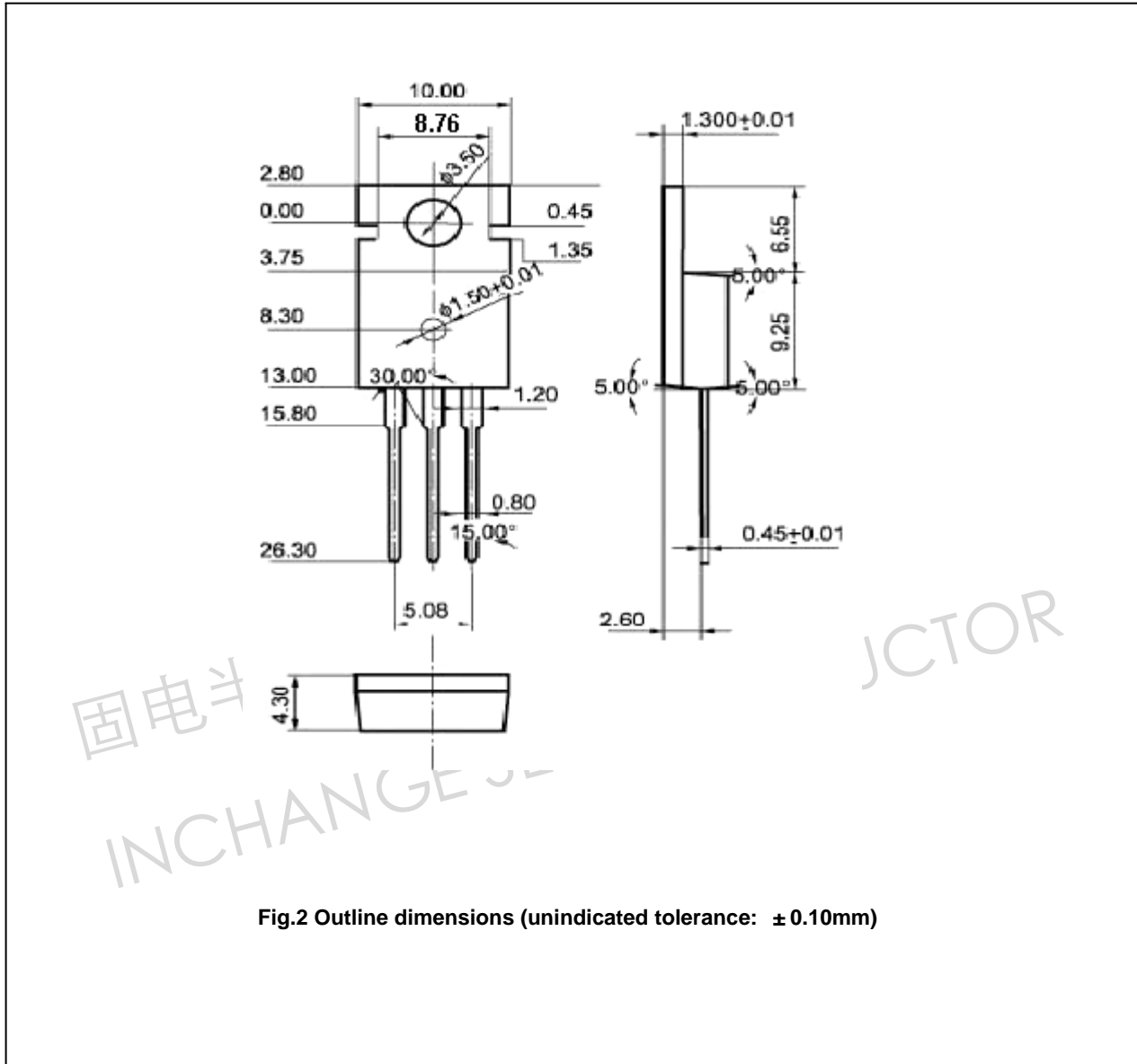


Fig.2 Outline dimensions (unindicated tolerance: ±0.10mm)